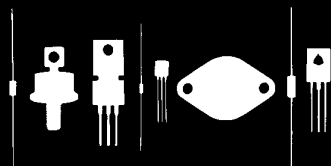


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CBR10F-010P SERIES
CBR25F-010P SERIES
CBR35F-010P SERIES

FAST RECOVERY
SILICON BRIDGE RECTIFIERS

10 THRU 35A, 100 THRU 600V

DESCRIPTION

- The CENTRAL SEMICONDUCTOR CBR10F, CBR25F, CBR35F series types are silicon single phase full wave bridge rectifiers designed for fast recovery applications.
- Standard recovery devices are also available .
- The plastic material used carries Underwriters Laboratory flammability classification 94V-0.
- Utilizes standard 0.25" fast on connectors.
- Wire leaded devices available by adding suffix "W" to part no. (ex: CBR35F-060PW).

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	-010P	-020P	-040P	-060P	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	V
DC Blocking Voltage	V_R	100	200	400	600	V
RMS Reverse Voltage	$V_R(RMS)$	70	140	280	420	V

Average Forward Current ($T_C=60^\circ\text{C}$)

	I_0	
CBR10F-010P SERIES	10	A
CBR25F-010P SERIES	25	A
CBR35F-010P SERIES	35	A

Peak Forward Surge Current (JEDEC)

	I_{FSM}	
CBR10F-010P SERIES	200	A
CBR25F-010P SERIES	300	A
CBR35F-010P SERIES	400	A

Operating and Storage Junction Temperature

T_J, T_{STG}	-65 to +150	$^\circ\text{C}$
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Maximum Thermal Resistance

θ_{JC}	1.5	$^\circ\text{C/W}$
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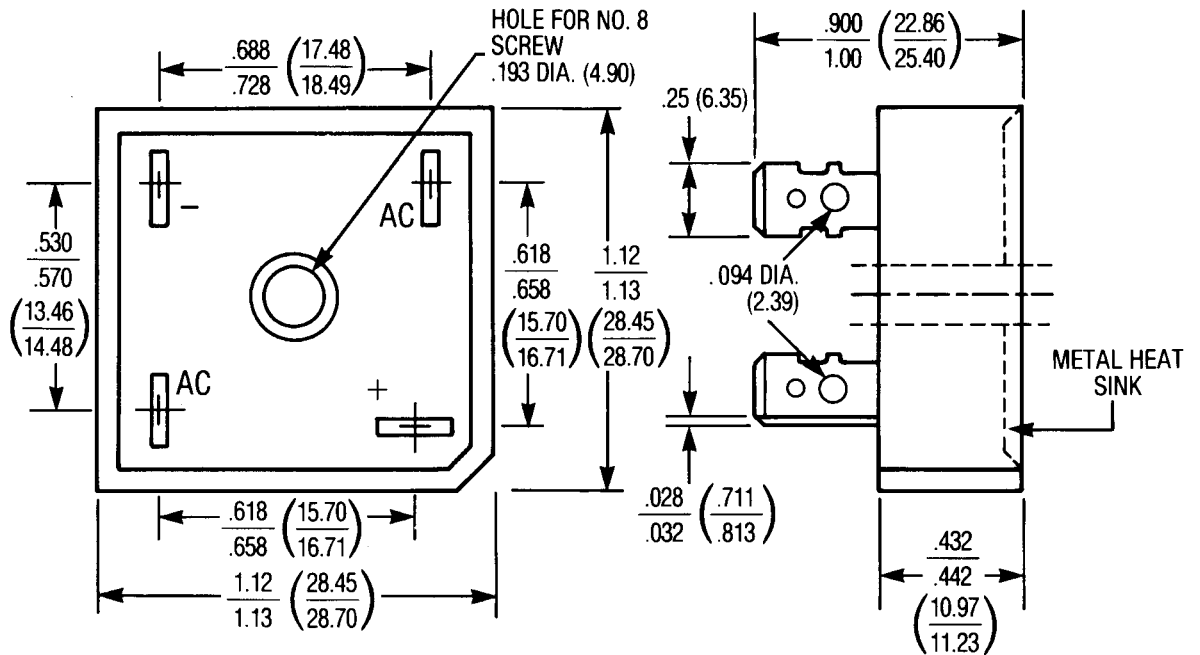
Isolation Voltage (case to leads)

V_{iso}	2500	Vac
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ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

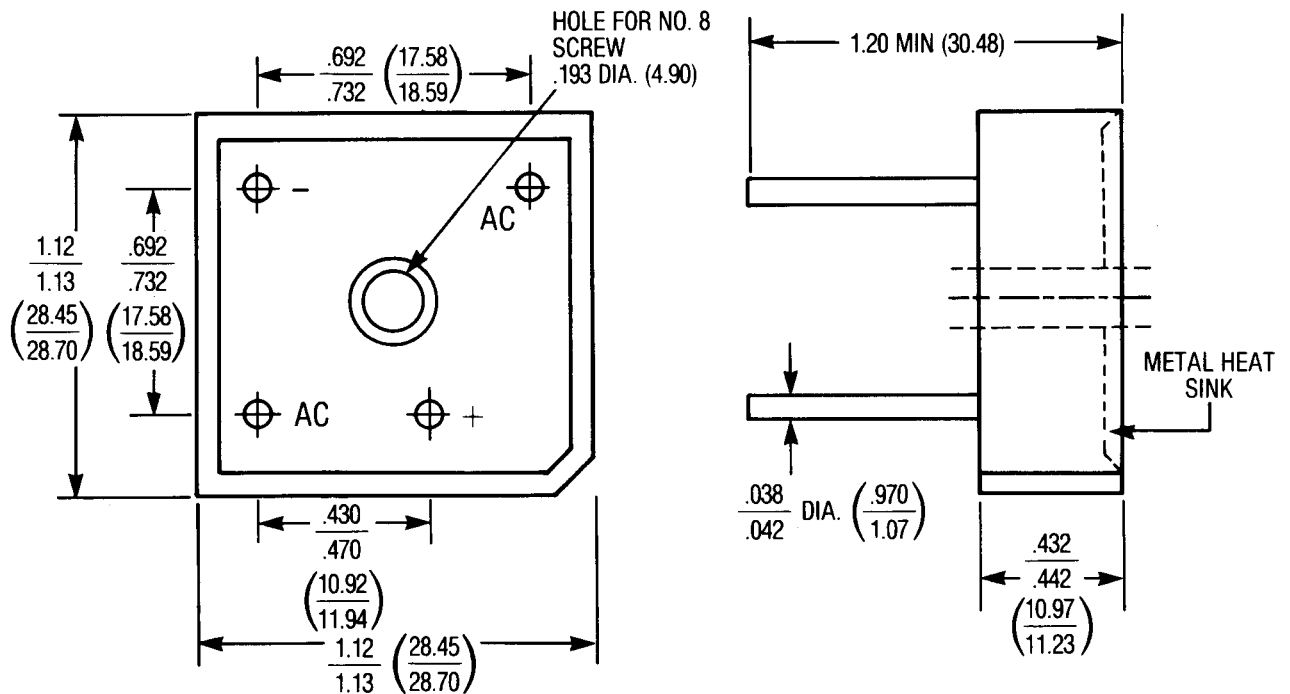
		MIN	MAX	UNIT
V_F	$I_F=\frac{1}{2}$ Rated I_0		1.3	V
I_R	$V_R=\text{Rated } V_{RRM}$		10	μA
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$ (-010P thru -040P)		200	ns
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$ (-060P)		350	ns

-010P SERIES



DIMENSIONS IN INCHES (MILLIMETERS)

-010PW SERIES



DIMENSIONS IN INCHES (MILLIMETERS)